# 2SD1823G

### Silicon NPN epitaxial planar type

For low-frequency amplification

#### Features

- High forward current transfer ratio  $h_{FE}$
- $\bullet$  Low collector-emitter saturation voltage  $V_{CE(sat)}$
- $\bullet$  High emitter-base voltage (Collector open)  $V_{EBO}$
- Low noise voltage NV
- S-Mini type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.
- Package
- Code
  - SMini3-F2
- Marking Symbol: 1Z
- Pin Name
  - 1: Base
  - 2: Emitter
  - 3: Collector

Parameter	Symbol	Rating	Unit	
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	50	v	
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	40	V	
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	15	V	
Collector current	I <sub>C</sub>	50	mA	
Peak collector current	I <sub>CP</sub>	100	mA	
Collector power dissipation	P <sub>C</sub>	150	mW	
Junction temperature	Tj	150	°C	
Storage temperature	T <sub>stg</sub>	-55 to +150	°C	

#### Absolute Maximum Ratings $T_a = 25^{\circ}C$

#### Electrical Characteristics $T_a = 25^{\circ}C \pm 3^{\circ}C$

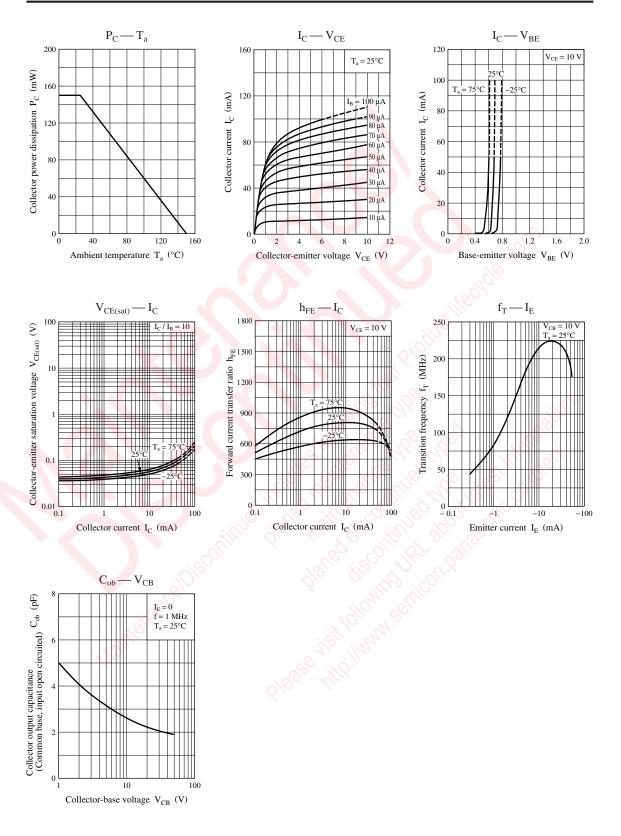
Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Collector-base voltage (Emitter open)	V <sub>CBO</sub>	$I_{\rm C} = 10 \ \mu A, I_{\rm E} = 0$	50			V
Collector-emitter voltage (Base open)	V <sub>CEO</sub>	$I_{\rm C} = 1 \text{ mA}, I_{\rm B} = 0$	40			V
Emitter-base voltage (Collector open)	V <sub>EBO</sub>	$I_{\rm E} = 10 \ \mu A, I_{\rm C} = 0$	15			V
Collector-base cutoff current (Emitter open)	I <sub>CBO</sub>	$V_{CB} = 20 \text{ V}, I_E = 0$			0.1	μΑ
Collector-emitter cutoff current (Base open)	I <sub>CEO</sub>	$V_{CE} = 20 \text{ V}, I_B = 0$			1	μΑ
Forward current transfer ratio *	h <sub>FE</sub>	$V_{CE} = 10 \text{ V}, I_{C} = 2 \text{ mA}$	400		2 0 0 0	
Collector-emitter saturation voltage	V <sub>CE(sat)</sub>	$I_C = 10 \text{ mA}, I_B = 1 \text{ mA}$		0.05	0.20	V
Transition frequency	f <sub>T</sub>	$V_{CB} = 10 \text{ V}, I_E = -2 \text{ mA}, f = 200 \text{ MHz}$		120		MHz

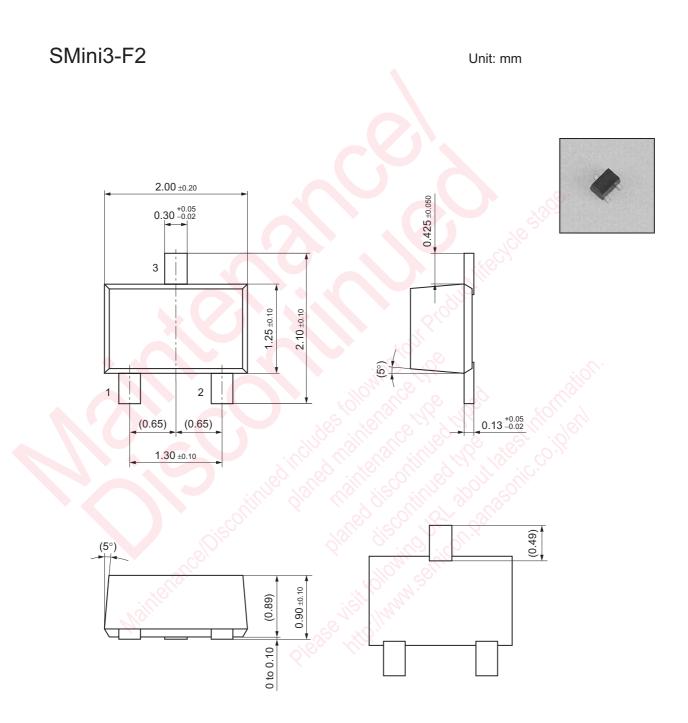
Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. \*: Rank classification

Rank	R	S	Т
$h_{\rm FE}$	400 to 800	600 to 1 200	1 000 to 2 000

### Panasonic





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